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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/797,183	03/11/2004	Taiji Ema	960045D	4954
38834	7590 04/21/2005		EXAMINER	
WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP 1250 CONNECTICUT AVENUE, NW			NGUYEN, CUONG QUANG	
SUITE 700	CIICOI AVENOE, IV	¥	ART UNIT PAPER NUMBER	
WASHINGTO	ON, DC 20036		2811	
	DATE MAILED: 04/2		DATE MAILED: 04/21/2005	S

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	\bigcirc
	10/797,183	EMA ET AL.	$(\mathcal{O} \mathcal{O})$
Office Action Summary	Examiner	Art Unit	
	Cuong Q. Nguyen	2811	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence add	ress
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period v - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this con D (35 U.S.C. § 133).	
Status			
3) Since this application is in condition for allowar	action is non-final. nce except for formal matters, pro		merits is
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 4:	53 O.G. 213.	
Disposition of Claims			
4) ⊠ Claim(s) <u>1-6</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdray 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) <u>1-4 and 6</u> is/are rejected. 7) ⊠ Claim(s) <u>5</u> is/are objected to. 8) □ Claim(s) are subject to restriction and/o			
Application Papers			
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomposed and applicant may not request that any objection to the Replacement drawing sheet(s) including the correct and the contract of the	epted or b) objected to by the didentified or b) objected to by the drawing(s) be held in abeyance. Set ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFF	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	ion No ed in this National S	Stage
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:	ate	-152)

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DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claim 4 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. There is no support for limitation "the opening is not filled with the capacitor storage electrode" in the original specification of in the figures. It is noted that, in Fig.34, the capacitor storage electrode is filled partially the opening.

2. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 4 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. The limitation "the opening is not filled with the capacitor storage electrode" in claim 4 is contradict to the limitation "capacitor storage electrode formed on an inside wall...... of the opening" which means the capacitor storage electrode has to be filled the opening.

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Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-3 and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Miki et al. (US 5,499,207) in view of Miyake (US 5,403,766).

Regarding claims 1, 3 and 6, Miki et al. discloses a semiconductor storage device comprising: a memory cell transistor (a MOS transistor) inherently having a first diffused layer (a first source/drain layer of the MOS transistor) and a second diffused layer (a second source/drain layer of MOS transistor) formed in a semiconductor substrate, and a gate electrode formed over the semiconductor substrate between the first diffused layer and the second diffused layer with a gate insulation film interposed therebetween (col.4 lines 55-67); an insulation film including a layer (102) of phosphorous glass layer (col.5 lines 5-10) and a layer (603) having different etching characteristic from the layer (102) over the (102) layer covering a top of the memory cell transistor and having a through-hole opened in the layer (102) on the first diffused layer and an opening in the layer (603) surrounding the through-hole, the opening having a larger diameter than the

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through-hole and not reaching the semiconductor substrate; a capacitor storage electrode (104) formed on and along an inside wall and a bottom of the opening and electrically connected to the substrate; a capacitor dielectric film (601) formed covering the capacitor storage electrode; and a capacitor opposed electrode (602) formed covering the capacitor dielectric film. See Miki et al.'s Fig.6.

Miki et al.'s Fig.6 does not explicitly show that the capacitor storage electrode electrically connected to the first diffused layer.

It is conventional and also taught by Miyake's Fig.1C that the capacitor storage electrode commonly formed to electrically connect to the first diffused layer of MOS transistor (memory transistor) in order to store the information from the second diffused layer (the bit line of memory).

It would have been obvious to one of ordinary skill in the art to form Miki et al.'s memory device such as the capacitor storage electrode electrically connecting to the first diffused layer of the memory MOS transistor as taught by Miyake in order to stor the information in the capacitor storage electrode when the memory transistor is on state.

Regarding claim 2, as shown in Miki et al.'s Fig.6, the capacitor storage electrode includes a columnar conductor (105) buried in the through-hole and projected in the opening (above the bottom surface of the opening which is an upper surface of layer 102).

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Allowable Subject Matter

4. Claim 5 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

5. The following is an examiner's statement of reasons for allowance: above combination appears to be the closest prior art reference. However, this combination fails to teach that a thickness of the capacitor storage electrode is thinner than a depth of the opening. Prior art of record fails to teach or suggest to incorporate these limitations above references to arrive at the claimed device.

Response to Arguments

6. Applicant's arguments filed on 02-01-05 have been fully considered but they are not persuasive. Applicants argue that Miki et al. does not teach the bottom electrode is formed on and in contact with the bottom of the opening. It is noted that the features upon which applicant relies (i.e., the bottom electrode is in contact with the bottom of the opening) are not recited in the rejected claim(s). Although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See *In re Van Geuns*, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993). It is noted that "on" does not mean "in contact".

Conclusion

7. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

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A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

- 8. Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 872-9306. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.
- 9. Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to CUONG Q NGUYEN whose telephone number is (571) 272-1661. The Examiner is in the Office generally between the hours of 6:30 AM to 5:00 PM (Eastern Standard Time) Monday through Thursday.
- 10. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor Eddie Lee who can be reached on (571) 272-1732.

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11. Any inquiry of a general nature or relating to the status of this application should be directed to the Technology Center Receptionists whose telephone number is 308-0956.

Cuong Nguyer

Primary examiner

4/13/05